Supporting Information

High-aspect-ratio Photoresist Nanopillar Arrays with Broadband Near-perfect Optical Absorption Performance Using PDMS-Assisted Colloidal Lithography

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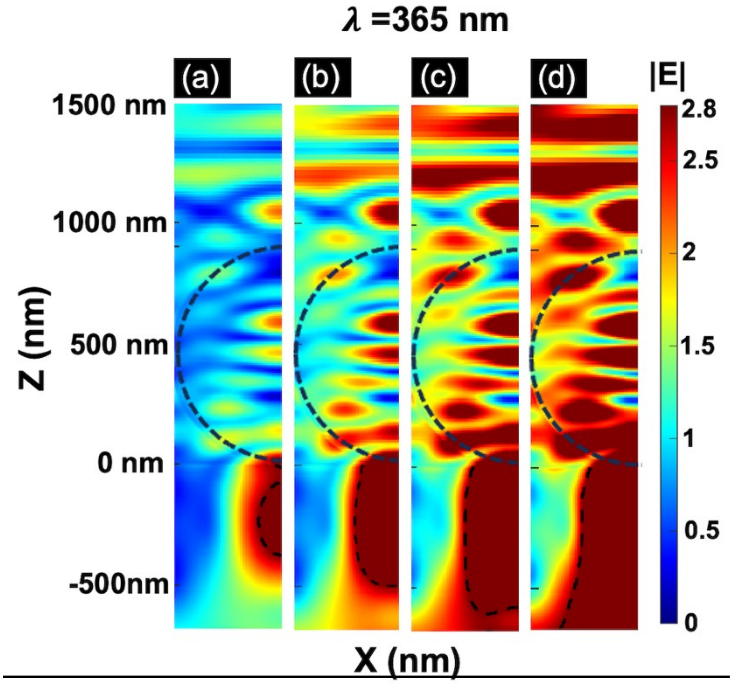

Figure S1a-d. Electric field distributions showing the region above the threshold for effective exposure under ultraviolet light source with different light intensity of (a)1, (b)1.5, (c)2, (d)2.5 times of the original light intensity. The dashed line showing the edge of effective exposure region when the electric field intensity of 2.8 times of the origin light source is considered as the threshold.